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## Introduction

The tables presented here are a compilation of data pertinent to near-backscattering, spherical analyzers for Resonant Inelastic X-ray Scattering (RIXS) measurements. They contain viable crystal reflections for absorption edge- and emission line energies in the hard x-ray range, together with reflection strength- and resolution information. They assume a sample-analyzerdetector geometry based on a Rowland circle with a position-sensitive (strip-) detector as described under [Detector-Analyzer Geometry]. Crystal materials included are Si, Ge, Lithium Niobate (LiNbO<sub>3</sub>), Sapphire (Al<sub>2</sub>O<sub>3</sub>) and Quartz (SiO<sub>2</sub>).

Structure factors involved in generating the reflection data were calculated for room temperature (RT=293.15 K), using Debye-Waller factors e<sup>-2M</sup> with

$$e^{-M} = \sqrt{e^{-2M}} = e^{-B_{RT} \left(\frac{\sin \Theta}{\lambda}\right)}$$
 (0)

where  $\sin\Theta/\lambda$  is proportional to the momentum transfer, and mean-square atomic vibrational amplitudes B<sub>RT</sub> were derived from x-ray diffraction measurements. In particular, the following vibrational amplitudes  $B_{RT}$  and associated Debye temperatures  $\Theta_D$  were used:

	$B_{RT}$	$\Theta_{ m D}$
	$[\mathring{A}^2]$	[K]
Si	$0.4632^{3)}$	530.82
Ge	0.5661 4)	290.03
LiNbO <sub>3</sub>	Li: 0.5264 <sup>5)</sup>	1118.44
	Nb: 0.4174	298.90
	O: 0.5738	643.27
$Al_2O_3$	Al: 0.1921 <sup>6)</sup>	897.40
	O: 0.2271	1122.51
$SiO_2$	Si: 0.4874 <sup>7)</sup>	516.38
	O: 0.9949	476.16

## References

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